TOSHIBA Transistor Silicon NPN Epitaxial Type (PCT Process)

# 2SC3709A

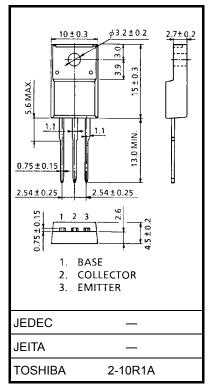
### **High-Current Switching Applications**

Unit: mm

- Low collector saturation voltage: VCE (sat) = 0.4 V (max)
- High-speed switching:  $t_{stg} = 1.0 \mu s$  (typ.)
- Complementary to 2SA1451A

### **Absolute Maximum Ratings (Tc = 25°C)**

Characteristics	Symbol	Rating	Unit
Collector-base voltage	$V_{CBO}$	60	V
Collector-emitter voltage	V <sub>CEO</sub>	50	V
Emitter-base voltage	V <sub>EBO</sub>	6	V
Collector current	IC	12	Α
Base current	ΙB	2	Α
Collector power dissipation (Tc = 25°C)	P <sub>C</sub>	30	W
Junction temperature	Tj	150	°C
Storage temperature range	T <sub>stg</sub>	−55 to 150	°C



Weight: 1.7 g (typ.)

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the

reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/Derating Concept and Methods) and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

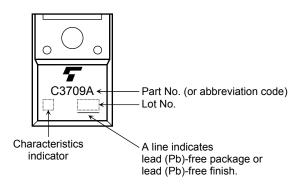


## **Electrical Characteristics (Tc = 25°C)**

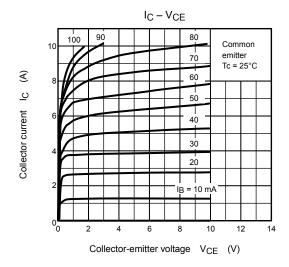
Chara	acteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Collector cut-off of	current	I <sub>CBO</sub>	V <sub>CB</sub> = 60 V, I <sub>E</sub> = 0	_	_	10	μA
Emitter cut-off cur	rrent	I <sub>EBO</sub>	V <sub>EB</sub> = 6 V, I <sub>C</sub> = 0	_	_	10	μΑ
Collector-emitter	breakdown voltage	V (BR) CEO	I <sub>C</sub> = 50 mA, I <sub>B</sub> = 0	50	_	_	V
DC current gain		h <sub>FE (1)</sub> (Note)	V <sub>CE</sub> = 1 V, I <sub>C</sub> = 1 A	70	_	240	
		h <sub>FE</sub> (2)	V <sub>CE</sub> = 1 V, I <sub>C</sub> = 6 A	40	_	_	
Collector-emitter	saturation voltage	V <sub>CE</sub> (sat)	I <sub>C</sub> = 6 A, I <sub>B</sub> = 0.3 A	_	0.25	0.4	V
Base-emitter satu	ıration voltage	V <sub>BE</sub> (sat)	I <sub>C</sub> = 6 A, I <sub>B</sub> = 0.3 A	_	0.9	1.2	V
Transition frequer	ncy	f <sub>T</sub>	V <sub>CE</sub> = 5 V, I <sub>C</sub> = 1 A	_	90	_	MHz
Collector output capacitance		C <sub>ob</sub>	V <sub>CB</sub> = 10 V, I <sub>E</sub> = 0, f = 1 MHz	_	180	_	pF
Switching time St	Turn-on time	t <sub>on</sub>	$^{20}$ μs $^{1}$ $^$	_	0.2	_	
	Storage time	t <sub>stg</sub>			1.0		μs
	Fall time	t <sub>f</sub>		_	0.2	_	

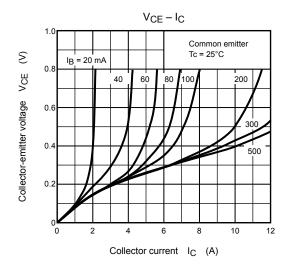
Note:  $h_{FE}$  (1) classification O: 70 to 140, Y: 120 to 240

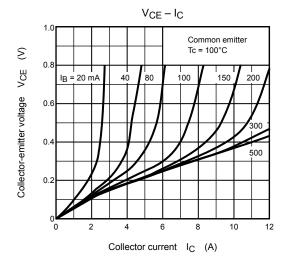
### Marking

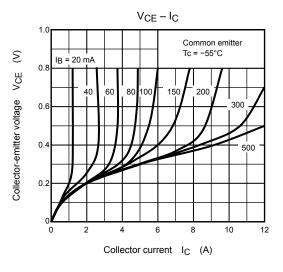


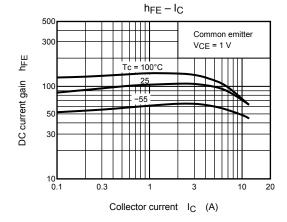
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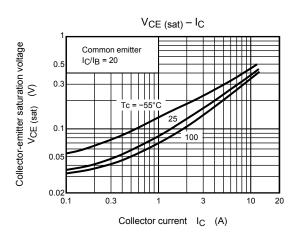




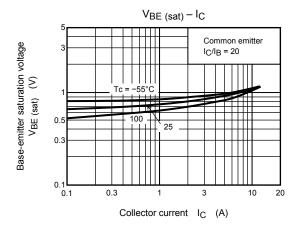


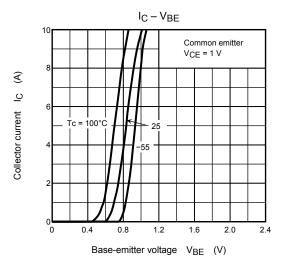


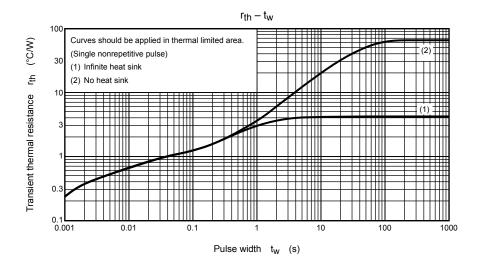


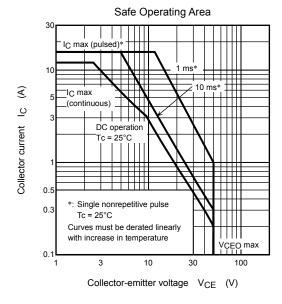


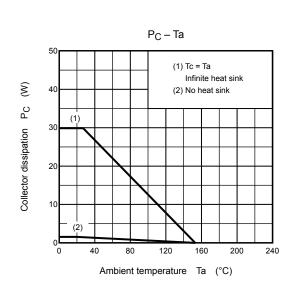
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